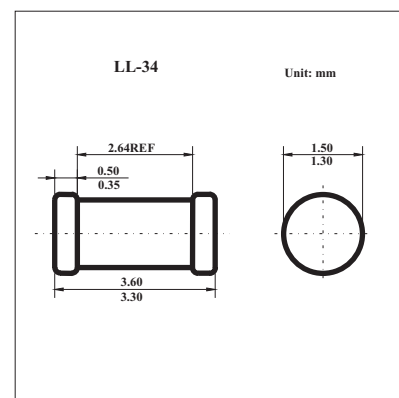


Band-switching diodes

BA682; BA683

■ Features

- Continuous reverse voltage: max. 35 V
- Continuous forward current: max. 100 mA
- Low diode capacitance: max. 1.5 pF
- Low diode forward resistance: max. 0.7 to 1.2 Ω

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			35	V
Continuous forward current	I_F	single diode loaded		100	mA
Storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
Junction temperature	T_j			150	$^\circ\text{C}$
Thermal resistance from junction to tie-point	$R_{th\ j-t\ p}$			300	K/W
Thermal resistance from junction to ambient	$R_{th\ j-a}$			600	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Max	Unit
Forward voltage	V_F	$I_F = 100\text{ mA}$	1.0	V
Reverse current	I_R	$V_R = 20\text{ V}$	50	nA
		$V_R = 20\text{ V}; T_j = 75^\circ\text{C}$	1	$\mu\text{ A}$
Diode capacitance	C_d	$f = 1\text{ MHz}; V_R = 1\text{ V}$	1.5	pF
Diode capacitance	C_d	$f = 1\text{ MHz}; V_R = 3\text{ V}$	1.25	pF
			1.20	
Diode forward resistance	r_D	$I_F = 3\text{ mA}; f = 200\text{ MHz};$	0.7	Ω
			1.2	
Diode forward resistance	r_D	$I_F = 10\text{ mA}; f = 200\text{ MHz};$	0.5	Ω
			0.9	